



Bipolar NPN Bare Die – BTN979

Part Description

The BTN979 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 100V
- VCEO = 80V
- VEBO = 5V
- hFE = 210-390 @ VCE = 3V, IC = 0.5A
- VCE(Sat) = 0.4V @ IC = 0.5A, IB = 20mA
- fT = 140 MHz @ VCE = 10V, IE = 0A
- COBO = 11pF @ VCB = 10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to ROHM 2SD1898. Smaller die size.

Die Size (Unawn)

920µm X 920µm, 36 Mils X 36 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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